

L34F3C
L34SF4C

L34F3BT
L34SF4BT

Features

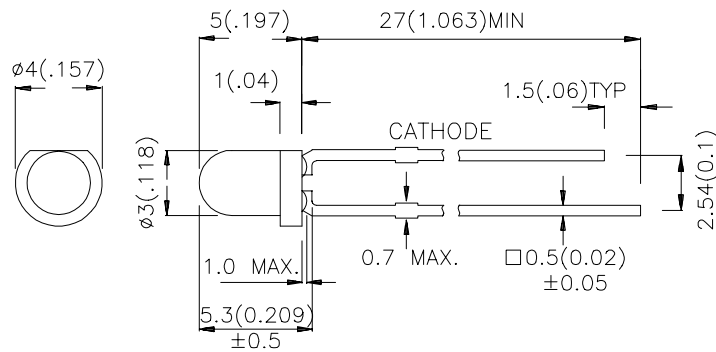
- MECHANICALLY AND SPECTRALLY MATCHED TO THE L32P3C PHOTOTRANSISTOR.
- BOTH WATER CLEAR LENS AND BLUE TRANSPARENT LENS AVAILABLE HIGH POWER OUTPUT.

Description

F3 Made with Gallium Arsenide Infrared Emitting diodes.

SF4 Made with Gallium Aluminum Arsenide Infrared Emitting diodes.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

Selection Guide

Part No.	Dice	Lens Type	Po (mW/sr) @20mA		Po (mW/sr) @50mA		Viewing Angle
			Min.	Typ.	Min.	Typ.	
L34F3C	GaAs	WATER CLEAR	2	10	5	20	50°
L34F3BT	GaAs	BLUE TRANSPARENT	2	5	8	20	50°
L34SF4C	GaAlAs	WATER CLEAR	2	10	5	20	50°
L34SF4BT	GaAlAs	BLUE TRANSPARENT	2	4	8	20	50°

Note:

1. $\theta 1/2$ is the angle from optical centerline where the luminous intensity is 1/2 the optical centerline value.

Electrical / Optical Characteristics at $T_A=25^\circ\text{C}$

Item	P/N	Symbol	Typ.	Max.	Unit	Condition
Forward Voltage	F3 SF4	V_F	1.2 1.3	1.5 1.7	V	IF=20mA
Reverse Current	F3 SF4	I_R	-	10 10	uA	VR=5V
Junction Capacitance	F3 SF4	C	90 90	-	pF	V=0 f=1MHz
Peak Spectral Wavelength	F3 SF4	λ_P	940 880	-	nm	IF=20mA
Spectral Bandwidth	F3 SF4	$\Delta\lambda$	50 50	-	nm	IF=20mA

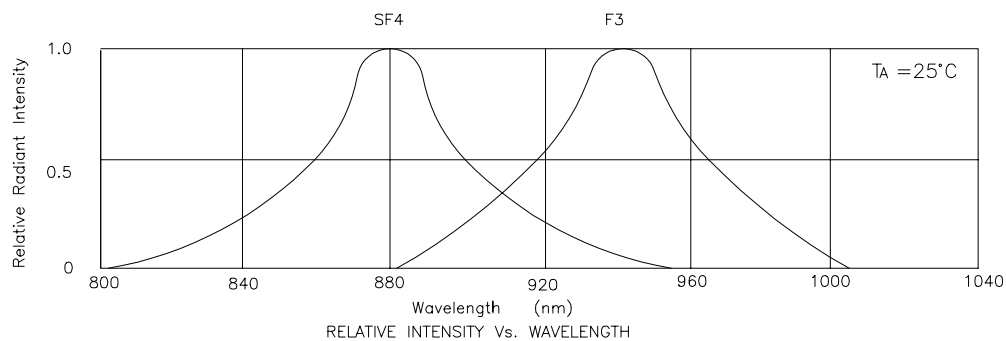
Absolute Maximum Ratings at $T_A=25^\circ\text{C}$

Item	Symbol	F3&SF4	Units
Power Dissipation	PT	100	mW
Forward Current	I_F	50	mA
Peak Forward Current	I_P	1.2	A
Reverse Voltage	V_R	5	V
Operating Temperature	T_A	-40~ +85	°C
Storage Temperature	T_{stg}	-40~ +85	°C

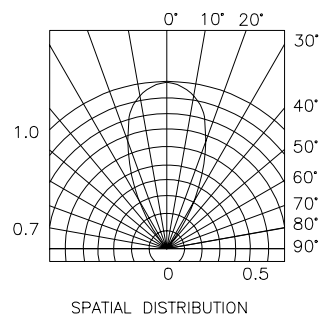
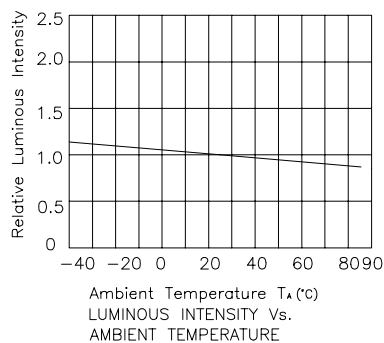
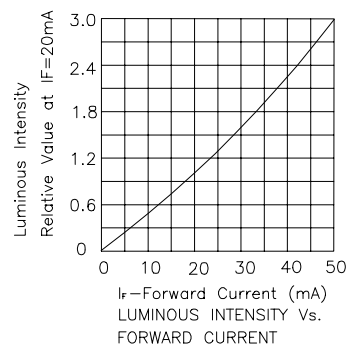
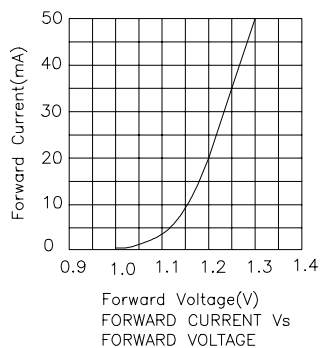
Notes:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.

2. 4mm below package base.



L34F3C, L34F3BT



L34SF4C, L34SF4BT

